

## Silicon NPN Power Transistors 2N5622 2N5624 2N5626 2N5628

### DESCRIPTION

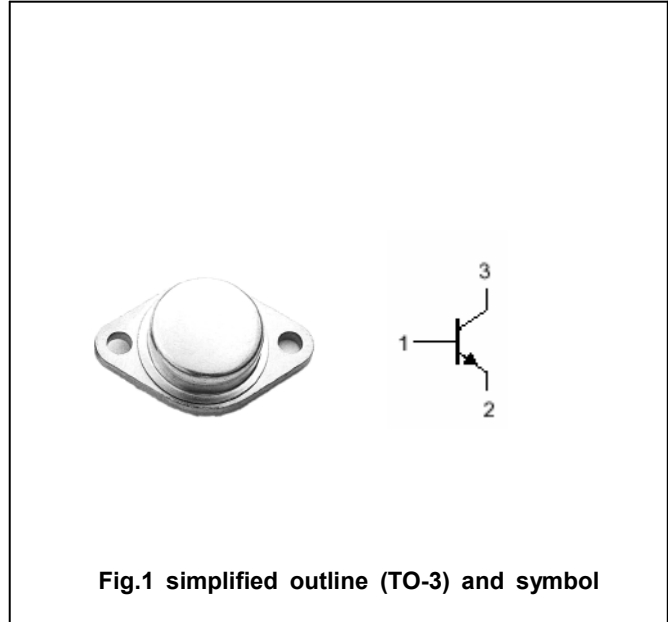
- With TO-3 package
- Excellent safe operating area
- Low collector saturation voltage

### APPLICATIONS

- For audio and general-purpose applications

### PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



### Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2N5622	80	V
		2N5624/5626	100	
		2N5628	120	
V <sub>CEO</sub>	Collector-emitter voltage	2N5622	60	V
		2N5624/5626	80	
		2N5628	100	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		10	A
P <sub>D</sub>	Total power dissipation	T <sub>C</sub> =25□	100	W
T <sub>j</sub>	Junction temperature		150	□
T <sub>stg</sub>	Storage temperature		-65~200	□

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-c</sub>	Thermal resistance junction to case	1.5	□/W

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**CHARACTERISTICS**T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	2N5622	I <sub>C</sub> =50mA ; I <sub>B</sub> =0	60			V
		2N5624/5626		80			
		2N5628		100			
V <sub>CEsat</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =10A; I <sub>B</sub> =1A			1.5	V
V <sub>BE</sub>	Base-emitter on voltage		I <sub>C</sub> =5A ; V <sub>CE</sub> =5V			1.5	V
I <sub>CBO</sub>	Collector cut-off current		V <sub>CB</sub> =Rated V <sub>CB0</sub> ; I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	2N5622/5626	I <sub>C</sub> =5A ; V <sub>CE</sub> =5V	70		200	
		2N5624/5628		30		90	
f <sub>T</sub>	Transition frequency	2N5622/5626	I <sub>C</sub> =1A ; V <sub>CE</sub> =12V	40			MHz
		2N5624/5628		30			

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PACKAGE OUTLINE

